

Silicon PNP Power Transistor

2SA775

DESCRIPTION

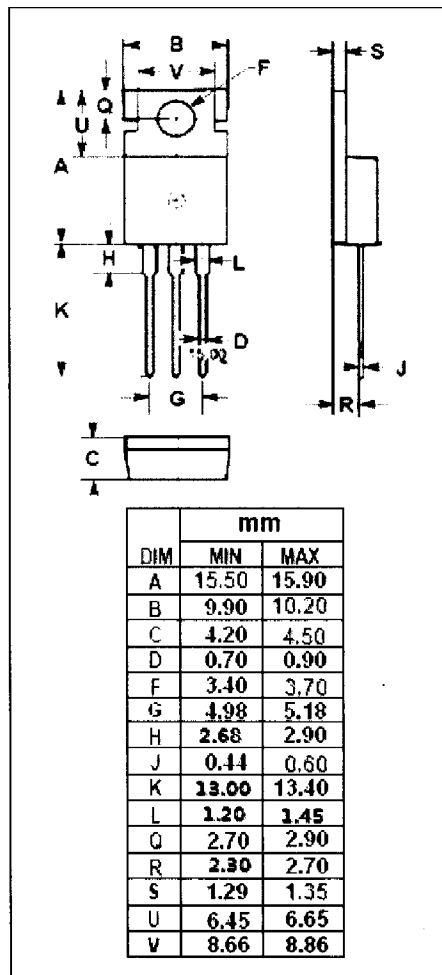
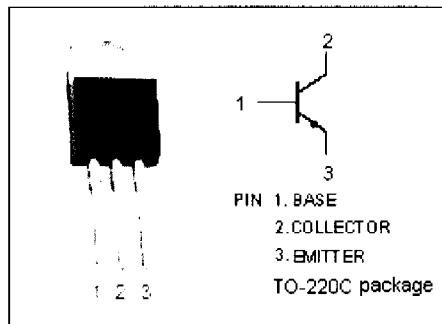
- Collector-Emitter Breakdown Voltage
 : $V_{(BR)CEO} = -100V(\text{Min})$
- Good Linearity of h_{FE}

APPLICATIONS

- Designed for general-purpose output amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_c	Collector Current-Continuous	-0.7	A
P_c	Total Power Dissipation @ $T_c=25^\circ\text{C}$	12.5	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=-10\text{mA}, I_B=0$	-100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=-10\mu\text{A}, I_E=0$	-100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=-10\mu\text{A}, I_C=0$	-4			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=-0.5\text{A}; I_B=-50\text{mA}$			-1.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=-100\text{V}; I_E=0$			-10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=-4\text{V}; I_C=0$			-10	μA
h_{FE}	DC Current Gain	$I_C=-50\text{mA}; V_{CE}=-4\text{V}$	35		200	
f_T	Current-Gain—Bandwidth Product	$I_C=-50\text{mA}; V_{CE}=-4\text{V}$	30			MHz